

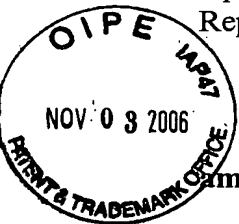
**IN THE SPECIFICATION**

**Please replace the paragraph beginning at page 12, line 25 with the following amended paragraph:**

In accordance with a tenth aspect of the present invention, there is provided the ring member including: a base material; and a film formed on a surface of the base material, wherein the film has a hydroxide layer formed of hydroxide including at least one kind of element in the Group 3a of the periodic table. ~~a base material and a film formed by spraying ceramic on the surface of the base material, wherein the film has a hydroxide layer formed of a hydroxide including at least one element of the Group 3A of the Periodic table.~~

**Please replace the paragraph beginning at page 27, line 16 with the following amended paragraph:**

Additionally, in accordance with the aforementioned embodiment, for example, when a plurality of processing vessels 2 are used for the same process, the adjustment of matching plasma shapes of these apparatuses can be readily performed. For example, when a plurality of the aforementioned plasma processing apparatuses described above are installed in a clean room and the same process is executed in these apparatuses, subtle differences may exist in process results of the wafers W because assembly of the apparatuses or the like are different slightly. However, in such a case, by adjusting voltages applied to the electrode 51, the characteristics of the apparatuses, i.e., the results of the process, can be ~~[[match]]~~ matched to each other. Thus, it can be easily achieved to match the apparatuses. For example, it is preferable that states of the processed wafers W are checked and an applied voltage for each apparatus is adjusted finely depending on the result. Further, the present invention is not limited to promoting the sharing of an apparatus and may be an apparatus for exclusive use in a certain type of process, e.g., etching of a specific film.



**Please replace the paragraph beginning at page 39, line 19 with the following**

**amended paragraph:**

On the other hand, “super ZAC” is a complex ceramic including  $\text{SiO}_2$  and  $\text{Cr}_2\text{O}_3$  as main ingredients, and has excellent heat-resistance and abrasion-resistance in addition to imporosity, high hardness and high adhesion. It is preferable to form the barrier coat layer 74 by a thermal spraying method. The thermal spraying method is a method for spraying raw material melted by a heat source such as combustion gas and electricity on a basic material to form a film. Further, the barrier layer 74 may be formed by employing a technique for forming a thin-film such as PVD and CVD method, an immersion method, a coating method, or the like. The PVD method is a method of coating various ceramic films coated at low temperature by employing an ion plating method, while the CVD method is a method for coating single layer or multiple layers at high temperature by a thermal chemical vapor deposition. Furthermore, the method is a method for performing a heat treatment after immersing various materials being immersed into a resin solution, and the coating method is a method for performing the heat treatment at a predetermined temperature after various materials being coated with a resin solution. It is desirable that the barrier coat layer 74 is of a thickness ranging from 50  $\mu\text{m}$  to 100  $\mu\text{m}$ .

**Please replace the paragraph beginning at page 42, line 5 with the following  
amended paragraph:**

Furthermore, an anodic oxidized film 75 may be formed between the base material 71 and the barrier coat layer 74 as depicted in Fig. 10. In this case, it is desirable that the anodic oxidized film is formed by organic acid, such as oxalic acid, chromic acid, phosphoric acid, acetic acid, formic acid or sulfonic acid, which will result in an oxidized film whose corrosion resistance is much better than those produced by an anodic oxidation treatment by sulfuric acid, so that it can further suppress the corrosion by the processing gas and the

Application No. 10/773,245  
Reply to Office Action of May 3, 2006

cleaning fluid. It is preferable that the anodic oxidized film 75 is of a thickness ranging from 10  $\mu\text{m}$  to 200  $\mu\text{m}$ .